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APPLICATION NO	D. FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/720,466	11/24/2003	Anthony Correale JR.	YOR920030373US1	4073
33233 7590 12/19/2005		EXAMINER		
	FICE OF CHARLES V	CHANG, DANIEL D		
11703 BOWMAN GREEN DRIVE SUITE 100		ART UNIT	PAPER NUMBER	
RESTON, VA 20190			2819	
		DATE MAILED: 12/10/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

EK	

•	Application No.	Applicant(s)				
Office Action Comment	10/720,466	CORREALE ET AL.				
Office Action Summary	Examiner	Art Unit				
	Daniel D. Chang	2819				
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply						
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).						
Status						
1) Responsive to communication(s) filed on 30 No	ovember 2005.					
·_ ·	action is non-final.					
3)☐ Since this application is in condition for allowan		secution as to the merits is				
·	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims						
4) Claim(s) 1-30 is/are pending in the application.						
4a) Of the above claim(s) is/are withdrawn from consideration.						
5) Claim(s) is/are allowed.						
6) Claim(s) 1-30 is/are rejected.						
7) Claim(s) is/are objected to.	alastian rasuisament					
8) Claim(s) are subject to restriction and/or	election requirement.					
Application Papers						
9) The specification is objected to by the Examiner	•					
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correction	on is required if the drawing(s) is obj	ected to. See 37 CFR 1.121(d).				
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).						
a) ☐ All b) ☐ Some * c) ☐ None of:						
1. Certified copies of the priority documents have been received.						
2. Certified copies of the priority documents have been received in Application No						
3. Copies of the certified copies of the priority documents have been received in this National Stage						
application from the International Bureau (PCT Rule 17.2(a)).						
* See the attached detailed Office action for a list of the certified copies not received.						
·						
Attachment(s)						
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 4) Interview Summary (PTO-413) Paper No(s)/Mail Date						
 3) Π Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) 		te atent Application (PTO-152)				
Paper No(s)/Mail Date 6) Other:						

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Acknowledgement

Receipt is acknowledged of the Amendment filed November 30, 2005.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-5, 7-9, 12-15, 18-23, and 25-27 rejected under 35 U.S.C. 102(b) as being anticipated by Foss (US 4,786,830).

Regarding claim 1, Foss discloses, in Fig. 2, a level converter for interfacing circuits supplied by different supply voltages, said level converter comprising:

a first buffer (20) receiving an input (21), said first buffer being connected between a virtual supply (25) and a supply return (Vss);

a second buffer (30) receiving an output (24) of said first buffer, connected between a first supply (Vcc) and said supply return (Vss); and

a supply select (6, 9) between said first supply and said virtual supply, said supply select receiving an output (26) from said second buffer and selectively passing a first supply voltage (Vdd) on said first supply or a reduced supply voltage (Vcc-voltage drop across 6; col. 3, lines 57+) to said virtual supply responsive to said output (26) from said second buffer, said reduced supply voltage being such that standby power is eliminated (col. 4, lines 10+) in said first buffer when said input is high.

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Regarding claim 2, Foss discloses, in Fig. 2, that said second buffer is an inverter (col. 3, lines 11+).

Regarding claim 3, Foss discloses, in Fig. 2, that said supply select is a supply switch (9) in parallel with at least one diode (6), both connected between said first supply and said virtual supply.

Regarding claim 4, Foss discloses, in Fig. 2, said supply switch (9) is a field effect transistor (FET)(col. 3, lines 55+) gated by said output (26) of said second buffer and said at least one diode is a diode connected FET (6).

Regarding claim 5, Foss discloses, in Fig. 2, that said supply switch FET is a P-type FET (PFET)(col. 3, lines 55+) and said at least one diode connected FET an N-type FET (NFET) diode (see 6).

Regarding claim 7, Foss discloses, in Fig. 2, that said second buffer is a CMOS inverter (col. 3, lines 9 and 21+).

Regarding claim 8, Foss discloses, in Fig. 2, that said first buffer is a CMOS inverter (col. 3, lines 9 and 21+).

Regarding claim 9, Foss discloses, in Fig. 2, that said first buffer is a logic gate (col. 3, lines 21+).

Regarding claim 12, Foss discloses, in Fig. 2, a voltage level converter circuit comprising:

a first inverter (20) with a first inverter input (21), a first inverter output (24), a first inverter ground (Vss) connected to a circuit ground (Vss), and a first inverter voltage supply (25);

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a threshold drop element (6) connected between a circuit high voltage supply (Vddh) (Vcc) and the first inverter voltage supply (25);

a second inverter (30) with a second inverter input connected to the first inverter output (24), a second inverter output (26), a second inverter ground connected to the circuit ground (Vss), and a second inverter voltage supply connected to Vddh (Vcc); and

a voltage feedback element (9) connected between Vddh (Vcc) and the first inverter voltage supply (25), the voltage feedback element having an input connected to the second inverter output (26), wherein when the second inverter output is low, the voltage feedback element causes the first inverter voltage supply to approach Vddh (since 9 turns ON) and making the first inverter output approach Vddh thereby eliminating a standby power in the second inverter (col. 4, lines 10+), and wherein when the second inverter output is high, standby power is substantially eliminated in the first inverter (col. 4, lines 10+).

Regarding claim 13, Foss discloses, in Fig. 2, that the threshold drop element (6) provides the first inverter voltage supply with a lower voltage than the circuit high voltage supply (col. 4, lines 28+) when the first inverter input is high (21).

Regarding claim 14, Foss discloses, in Fig. 2, that the threshold drop element is at least one transistor (6).

Regarding claim 15, Foss discloses, in Fig. 2, that the transistor is a field effect transistor (FET) (6).

Regarding claim 18, Foss discloses, in Fig. 2, that the threshold drop element is a diode (6).

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Regarding claim 19, Foss discloses, in Fig. 2, an integrated circuit (IC)(col. 1, lines 7+) comprising:

a plurality of circuit rows (inherent since COMOS input circuits are used in IC; col. 1, lines 7+);

at least one low voltage island (21) in at least one of said plurality of circuit rows, circuit elements (1, 2) in each said at least one low voltage island being powered by a low voltage (Vddl) supply (Vcc-VTH4; col. 3, lines 50+); and

at least one high voltage island (Vcc) in said at least one of said plurality of circuit rows, circuit elements in each said at least one high voltage island being powered by a high voltage (Vddh) supply (Vcc), Vddh being a higher voltage than Vddl (Vcc > Vcc-VTH4); and,

at least one level converter comprising:

a first buffer (20) receiving an input signal (21) from said at least one low voltage island, said first buffer being connected between a virtual supply (25) and a supply return (Vss);

a second buffer (30) receiving an output (24) of said first buffer and connected between Vddh (Vcc) and said supply return (Vss); and

a supply select (9) between Vddh (Vcc) and said virtual supply (25), said supply select receiving an output (26) from said second buffer and selectively passing Vddh (when 9 is ON) or a reduced supply voltage (Vcc-VTH6 when 9 is OFF) to said virtual supply responsive to said output from said second buffer.

Regarding claim 20, Foss discloses, in Fig. 2, that said second buffer is an invert (col. 3, lines 11+).

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Regarding claim 21, Foss discloses, in Fig. 2, that said supply select is a supply switch (9) in parallel with at least one diode (6), both connected between said first supply and said virtual supply.

Regarding claim 22, Foss discloses, in Fig. 2, said supply switch (9) is a field effect transistor (FET)(col. 3, lines 55+) gated by said output (26) of said second buffer and said at least one diode is a diode connected FET (6).

Regarding claim 23, Foss discloses, in Fig. 2, that said supply switch FET is a P-type FET (PFET)(col. 3, lines 55+) and said at least one diode connected FET an N-type FET (NFET) diode (see 6).

Regarding claim 25, Foss discloses, in Fig. 2, that said second buffer is a CMOS inverter (col. 3, lines 9 and 21+).

Regarding claim 26, Foss discloses, in Fig. 2, that said first buffer is a CMOS inverter (col. 3, lines 9 and 21+).

Regarding claim 27, Foss discloses, in Fig. 2, that said first buffer is a logic gate (col. 3, lines 21+).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 6, 16, 24, and 30 are rejected under 35 U.S.C. 103(a) as being unpatentable over Foss.

Regarding claims 6, 16, and 24, Foss discloses all the features of the claimed invention as discussed above but does not disclose that the at least one diode connected NFET is a plurality or a pair of series connected NFET diodes.

However, it is well known in the art that when more voltage drop is desired, more diodes are connected in series. Therefore, it would have been obvious at the time the invention was made to an ordinary skilled in the art to have added more well known NFET diode(s) in series with NFET diode (6) of Foss in order to provide more voltage drops.

Regarding claim 30, the modified Foss discussed above teaches a plurality of NFET diodes that reduces the reduced supply voltage below Vddl.

Claims 10 and 28 are rejected under 35 U.S.C. 103(a) as being unpatentable over Foss in view of Feller (EP 0 125 733 A1).

Foss discloses all the features of the claimed invention as discussed above but does not disclose that the first buffer is a NAND gate.

Feller discloses that the first buffer 10 can be any complementary FET arrangement including NAND gate (page 7, lines 16+).

Therefore, it would have been obvious to one of ordinary skill in the art at the time of applicant's invention to have provided the first buffer of Foss with the NAND gate as taught by Feller in order to use another function of complement FET arrangement.

Claims 11, 17, and 29 are rejected under 35 U.S.C. 103(a) as being unpatentable over Foss in view of Kao ("Dual Threshold Voltage Domino Logic", Sept. 1999).

Regarding claims 11 and 29, Foss discloses all the features of the claimed invention as discussed above but does not disclose that the output CMOS inverter includes an NFET having a threshold higher than other NFETs.

Kao discloses an output CMOS inverter (I1 in Fig. 1) with an NFET having a threshold higher than other NFETs for reducing leakage currents.

Therefore, it would have been obvious to one of ordinary skill in the art at the time of applicant's invention to have provided the CMOS inverter of Foss with the NFET having a threshold higher than other NFETs as taught by Kao in order to improve reducing leakage or standby currents.

Regarding claim 17, Foss discloses all the features of the claimed invention as discussed above but does not disclose that the FET is a high threshold voltage FET.

Kao discloses dual threshold devices comprising high threshold voltage FET (Pre-charge PMOS parallel with P1 in Fig. 1) for reducing leakage currents.

Therefore, it would have been obvious to one of ordinary skill in the art at the time of applicant's invention to have provided the FET (6) of Foss with the high threshold voltage FET as taught by Kao in order to improve reducing leakage or standby currents.

Response to Arguments

Applicant's request for reconsideration of the finality of the rejection of the last Office action is persuasive and, therefore, the finality of that action is withdrawn.

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Applicant's arguments with respect to claims 1-30 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Daniel D. Chang whose telephone number is (571) 272-1801. The examiner can normally be reached on Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Rexford Barnie can be reached on (571) 272-7492. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Daniel D. Chang Primary Examiner Art Unit 2819

DANIEL CHANG PRIMARY EXAMINER

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